

R.N.G.PATEL INSTITUTE OF TECHNOLOGY-RNGPIT
(An Autonomous College U/s UGC Act 1956)

B. Tech. SEMESTER-II, SEMESTER END EXAMINATION – SUMMER 2025

Subject Code: 1EL201

Date: 26-05-2025

Subject Name: BASIC ELECTRONICS

Time: 11:00 AM to 01:30 PM

Total Marks: 70

Instructions

1. It is **compulsory** for students to write **Enrolment No. /Seat No.** on the question paper.
2. Write answers of **Section A** and **Section B** in **separate answer books**.
3. Attempt all questions from both **Section A** and **Section B**.
4. Each section carries **35 marks**, with a total of **70 marks** for the examination.
5. The figures to the right of each question indicate full marks, make suitable assumptions with justification.
6. BL - Bloom's Taxonomy Levels (R-Remember, U-Understanding, A –Application, N –Analyze, E – Evaluate, C -Create), CO - Course Outcomes.

SECTION A

	Marks	BL	CO
Q.1 Multiple-Choice Questions	[05]		
(a) What is the use of a Rectifier circuit?	1	R	1
(i) To amplify the input signal (ii) To convert AC to DC supply (iii) To filter out (iv) To disturb the signal			
(b) The efficiency of Half Wave Rectifier is _____.	1	R	1
(i) 50% (ii) 40.6% (iii) 82% (iv) 45%			
(c) In Varactor Diode if Reverse voltage is increased, the capacitance is _____.	1	A	2
(i) increased (ii) No change (iii) decreased (iv) none of these			
(d) FET is a _____ device.	1	U	4
(i) Current Controlled (ii) Frequency Controlled (iii) Voltage Controlled (iv) none of these			

(e) What is the main advantage of FET which makes it more useful in industrial applications?	1	A	4
(i) Semiconductor device			
(ii) Less cost			
(iii) Voltage controlled operation			
(iv) Small size			

Q.2 Attempt Any Two	[10]		
(a) Explain V-I characteristics of P-N junction diode.	5	R	1
(b) Explain Full wave rectifier with necessary derivation (V_{dc} & V_{rms}) & waveforms.	5	A	1
(c) Classify Clamper circuits ad Explain any one clamper circuit.	5	N	1
Q.3 Attempt Any Two	[10]		
(a) Explain Zener diode ad its characteristics.	5	R	2
(b) Explain Varactor Diode.	5	U	2
(c) Explain Light Emitting Diode (LED).	5	R	2
Q.4 Attempt Any Two	[10]		
(a) Draw and Explain the construction, operation and characteristics of N-Channel JFET.	5	A	4
(b) Compare FET and BJT.	5	N	4
(c) Explain the construction, operation and characteristics N-Channel D-type MOSFET.	5	R	4

SECTION B

		Marks	BL	CO
Q.5 Multiple-Choice Questions	[05]			
(a) Input A='0' B='1' and C='1' for 3 –input Ex-OR gate. What is output?	1	U	5	
(i) '0'	(ii)'1'			
(iii) Toggle	(iv) High impedance state			
(b) In CE configuration of transistor , input circuit and output circuit are Reverse biased. So transistor will operate in	1	U	3	
(i) Active region	(ii) Saturation region			
(iii)Cut-OFF region	(iv) Highly saturation			
(c) 2's complement of decimal number “(17) ₁₀ ” in 8-bit binary format is	1	A	5	
(i) (0001 1000) ₂	(ii)(0001 0001) ₂			
(iii)(1111 0000) ₂	(iv)(1110 1111) ₂			
(d) Conversion of binary number (1000) ₂ to octal is	1	A	5	
(i)10	(ii)8			
(iii)0	(iv)5			
(e) In DC load line the co-ordinate (V _{ce} , I _c) at saturation point in CE configuration is	1	U	3	
(i) (0, I _c max)	(ii)(V _{cc} , 0)			
(iii)(V _{cc} , I _c max)	(iv) (0, 0)			
Q.6 Attempt Any Two	[10]			
(a) Explain working of NPN transistor with necessary diagrams.	5	R	3	
(b) Draw and explain voltage divider biasing with necessary equations. Enlist TWO advantages of voltage divider bias method compare to fixed bias method.	5	U	3	
(c) What is stability factor? Derive the expression for stability factor of collector feedback bias circuit .	5	U	3	
Q.7 Attempt Any Two	[10]			
(a) Make 2- input OR gate and AND gate using Diode circuit. Justify all logical input combination with resultant output of circuit.	5	U	5	
(b) What do you mean by universal gate? Enlist universal gates. Draw symbol and give truth table of each. Make OR gate using listed universal gate.	5	R	5	
(c) Give number conversion to binary , octal, hexadecimal, 1's complement, 2's complement, 9's complement and 10's complement of given decimal number (81) ₁₀	5	E	5	

Q.8 Attempt Any Two**[10]**

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|--|---|---|---|
| (a) It is desired to set operating point at 2V , 1mA by biasing silicon transistor with collector feedback resistor R_B . if $\beta = 100$, find the value of R_B . Draw the circuit diagram and mention all given and obtained values. | 5 | E | 3 |
| (b) Explain in detail : Transistor as Switch | 5 | A | 3 |
| (c) | 5 | E | 5 |
| (i) Using 2's complement, Find addition of $(35)_{10}$ with $(20)_{10}$ | | | |
| (ii) Using 2's complement, Find subtraction of $(35)_{10}$ with $(20)_{10}$ | | | |
| (iii) Using 9's complement, Find subtraction of $(35)_{10}$ with $(0001\ 0111)_2$ | | | |
